Dummy Pattern for Silicide Gate Electrode

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a plurality of silicided polysilicon structures in which the silicidation of the polysilicon structures is approximately uniform is provided. Dummy polysilicon structures are formed on the substrate prior to silicidation. The dummy polysilicon structures allow the surface of the wafer to be planarized without an excessive recess and causes the amount of metal available for the silicidation process to be approximately uniformly distributed among the various polysilicon structures.

(FIG. 4a)